

## GI32C

### PNP EPITAXIAL PLANAR TRANSISTOR

#### Description

The GI32C is designed for use in general purpose amplifier and switching applications.

#### Features

\*Complementary to GI31C

#### Package Dimensions

**TO-251**

**Marking :**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	7.20	7.80	K	0.45	0.60
E	2.30 REF.		L	0.90	1.50
F	0.60	0.90	M	5.40	5.80

#### Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

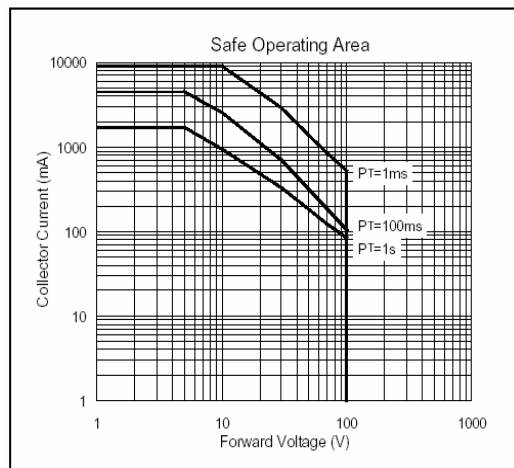
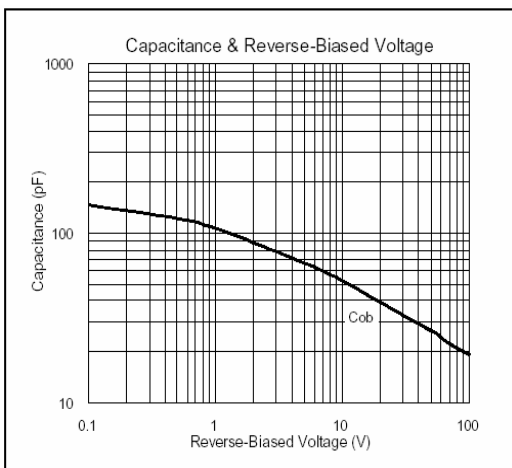
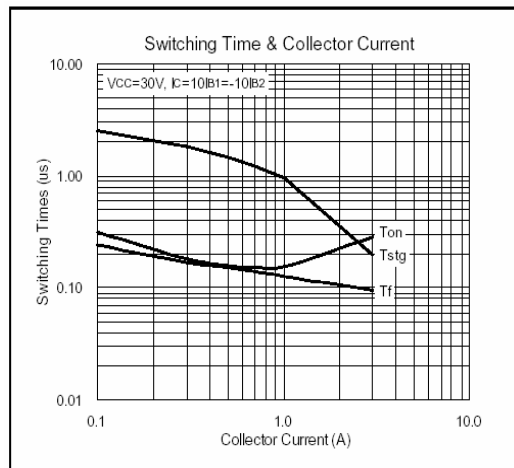
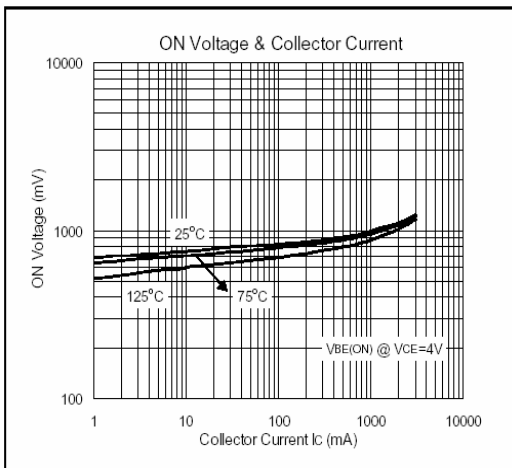
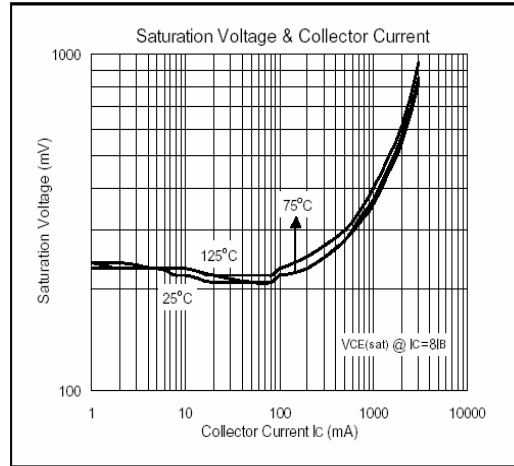
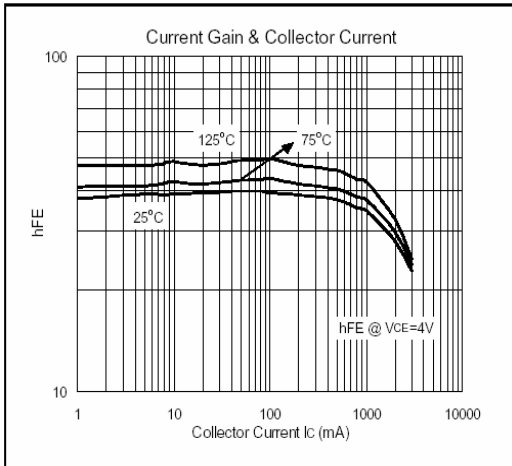
Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V <sub>CBO</sub>	-100	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-100	V
Emitter to Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current (DC)	I <sub>c</sub>	-3	A
Collector Current (Pulse)	I <sub>c</sub>	-5	A
Junction Temperature	T <sub>j</sub>	+150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C
Total Power Dissipation	PD	2	W
	PD(T <sub>C</sub> =25°C)	15	W

#### Electrical Characteristics (Rating at Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	-100	-	-	V	I <sub>C</sub> =-1mA, I <sub>E</sub> =0
BV <sub>CEO</sub>	-100	-	-	V	I <sub>C</sub> =-30mA, I <sub>B</sub> =0
BV <sub>EBO</sub>	-5	-	-	V	I <sub>E</sub> =-100uA, I <sub>C</sub> =0
I <sub>CES</sub>	-	-	-20	uA	V <sub>CE</sub> =-100V, V <sub>EB</sub> =0V
I <sub>CEO</sub>	-	-	-50	uA	V <sub>CE</sub> =-60V, I <sub>B</sub> =0
I <sub>EBO</sub>	-	-	-1	mA	V <sub>EB</sub> =-5V, I <sub>C</sub> =0
*V <sub>CE(sat)</sub>	-	-	-1.2	V	I <sub>C</sub> =-3A, I <sub>B</sub> =-375mA
*V <sub>BE(on)</sub>	-	-	-1.8	V	V <sub>CE</sub> =-4V, I <sub>C</sub> =-3A
*h <sub>FE1</sub>	25	-	-		V <sub>CE</sub> =-4V, I <sub>C</sub> =-1A
*h <sub>FE2</sub>	10	-	50		V <sub>CE</sub> =-4V, I <sub>C</sub> =-3A
f <sub>T</sub>	3	-	-	MHz	V <sub>CE</sub> =-10V, I <sub>C</sub> =-500mA, f=1MHz

\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

## Characteristics Curve



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**Head Office And Factory:**

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.  
 TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China  
 TEL : 86-21-5895-7671 FAX : 86-21-38950165